

N-Channel Power MOSFET

700V, 3.3A, 1.4Ω

FEATURES

- Super-Junction technology
- High performance due to small figure-of-merit
- High ruggedness performance
- High commutation performance

KEY PERFORMANCE PARAMETERS				
PARAMETER	ETER VALUE UNIT			
V_{DS}	700	V		
R _{DS(on)} (max)	1.4	Ω		
Q_g	7.7	nC		

Pb





APPLICATION

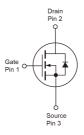
- Power Supply
- Lighting

TO-251 (IPAK)









Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _C = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	700	V	
Gate-Source Voltage		V_{GS}	±30	V	
Continuous Drain Current (Note 1)	$T_C = 25^{\circ}C$. I _D	3.3	А	
	$T_C = 100$ °C		2.0		
Pulsed Drain Current (Note 2)		I _{DM}	9.9	А	
Total Power Dissipation @ T _C = 25°C		P _{DTOT}	38	W	
Single Pulsed Avalanche Energy (Note 3)		E _{AS}	64	mJ	
Single Pulsed Avalanche Current (Note 3)		I _{AS}	1.6	А	
Operating Junction and Storage Temperatur	e Range	T_J , T_{STG}	- 55 to +150	°C	

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Case Thermal Resistance	R _{eJC}	3.3	°C/W	
Junction to Ambient Thermal Resistance	$R_{\Theta JA}$	62	°C/W	

Notes: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air.





ELECTRICAL SPECIFICATIONS (T _C = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	700			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	2	3	4	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 700V, V_{GS} = 0V$	I _{DSS}			1	μΑ
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 1.2A$	R _{DS(ON)}		0.9	1.4	Ω
Dynamic (Note 5)						
Total Gate Charge		Q_g		7.7		
Gate-Source Charge	$V_{DS} = 380V, I_{D} = 3.3A,$	Q_gs		1.9		nC
Gate-Drain Charge	$V_{GS} = 10V$	Q_{gd}		2.8		
Input Capacitance	$V_{DS} = 100V, V_{GS} = 0V,$	C _{iss}		370		
Output Capacitance	f = 1.0MHz	C _{oss}		34		pF
Gate Resistance	F = 1MHz, open drain	R_g		3.4		Ω
Switching (Note 6)						
Turn-On Delay Time		t _{d(on)}		14		
Turn-On Rise Time	$V_{DD} = 380V$,	t _r		22]
Turn-Off Delay Time	$R_{GEN} = 25\Omega,$ $I_D = 3.3A, V_{GS} = 10V,$	t _{d(off)}		24		ns
Turn-Off Fall Time		t _f		20		
Source-Drain Diode (Note 4)						
Forward On Voltage	I _S = 3.3A, V _{GS} = 0V	V _{SD}			1.4	V
Reverse Recovery Time	V _R = 200V, I _S = 2A	t _{rr}		163		ns
Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	Q _{rr}		1		μC

Notes:

- 1. Current limited by package
- 2. Pulse width limited by the maximum junction temperature
- 3. L = 50mH, $I_{AS} = 1.6A$, $V_{DD} = 50V$, $R_G = 25\Omega$, Starting $T_J = 25^{\circ}C$
- 4. Pulse test: PW \leq 300 μ s, duty cycle \leq 2%
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.





ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM70N1R4CH C5G	TO-251 (IPAK)	75pcs / Tube
TSM70N1R4CP ROG	TO-252 (DPAK)	2,500pcs / 13" Reel

Note:

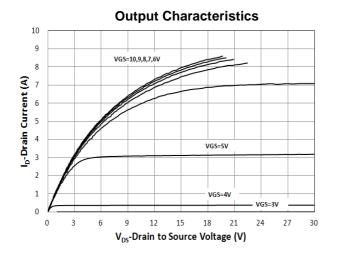
- 1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- 2. Halogen-free according to IEC 61249-2-21 definition





CHARACTERISTICS CURVES

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$



Transfer Characteristics

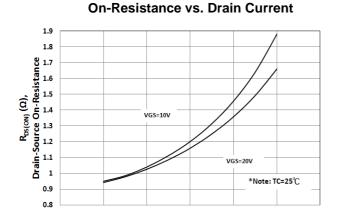
Vds=10V

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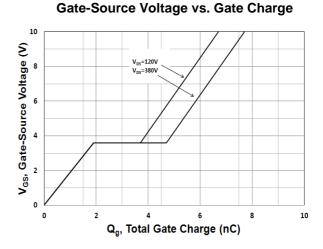
150C

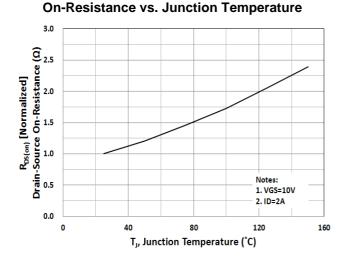
25C

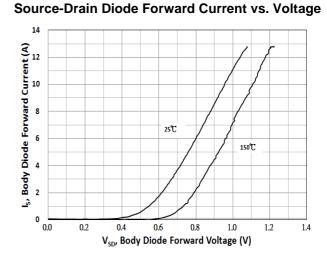
Vgs Gate to Source Voltage



I_D, Drain Current (A)







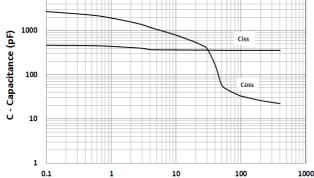


CHARACTERISTICS CURVES

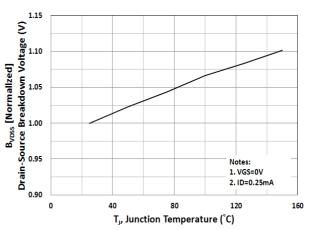
 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$



Capacitance vs. Drain-Source Voltage

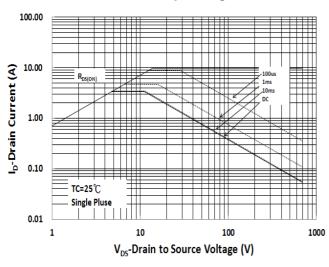


BV_{DSS} vs. Junction Temperature

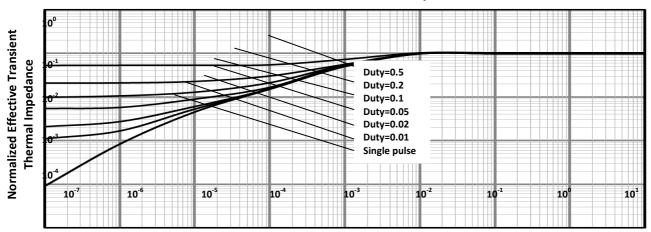


Maximum Safe Operating Area

 \mathbf{V}_{DS} - Drain to Source Voltage (V)





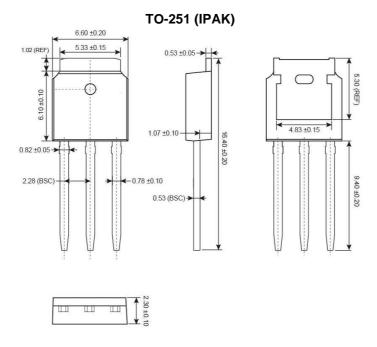


Square Wave Pulse Duration (sec)

10¹



PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



MARKING DIAGRAM



Y = Year Code

M = Month Code for Halogen Free Product

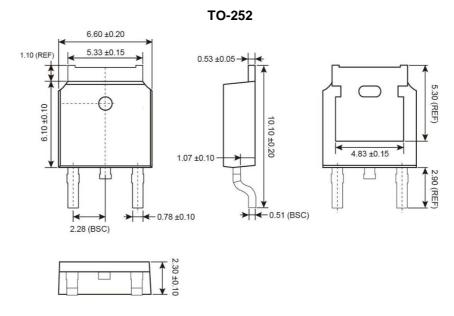
O =Jan **P** =Feb **Q** =Mar \mathbf{R} =Apr **S** =May **T** =Jun **U** =Jul V =Aug W =Sep X =Oct **Z** =Dec

Y =Nov

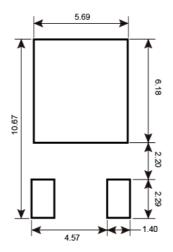
L = Lot Code (1~9, A~Z)



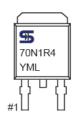
PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



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